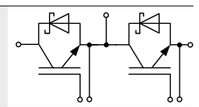
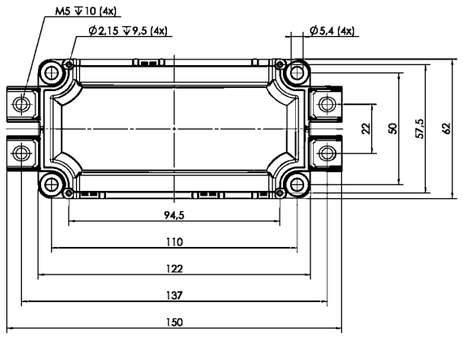
SiC Modules / Hybrid SiC / SEMiX

Type	IGBT						Diode			Module		
	I_C @ T_C = 25°C	Current (A)	$V_{CE(sat)}$ @ T_j = 25°C typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ T_C = 25°C	V_F	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	K/W		K/W	Circuit
1200V - IGBT4 (Trench)												
SEMiX603GB12E4SiCp	1110	600	1.80	17	72	0.037	404	1.40	0.14	3p	0.012	

Footnotes: 1) Sample status

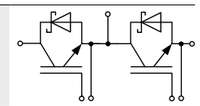
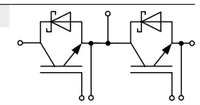
Cases

SEMiX 3p



Dimensions in mm

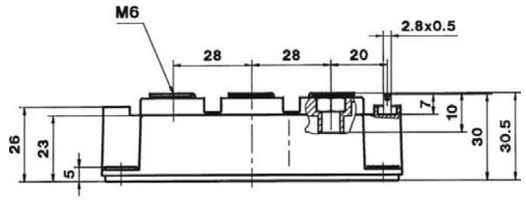
SiC Modules / Hybrid SiC / SEMITRANS

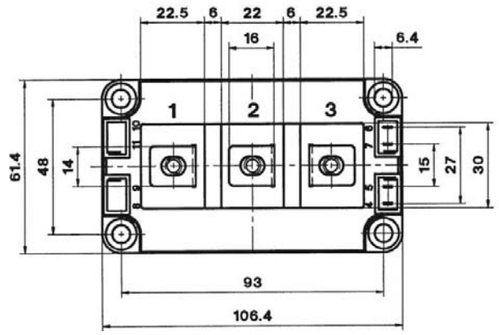
Type	IGBT						Diode			Module		
	I_C @ T_C = 25°C	Current (A)	$V_{CE(sat)}$ @ T_j = 25°C typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ T_C = 25°C	V_F	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	K/W		K/W	Circuit
1200V - IGBT4 (Trench)												
SKM200GB12T4SiC2 [1)]	313	200	1.80	7	20	0.14	246	1.40	0.21	3	0.038	
1200V - IGBT4 (Fast Trench)												
SKM200GB12F4SiC2[1)]	279	200	2.06	7	17	0.14	246	1.40	0.21	3	0.038	
SKM200GB12F4SiC3[1)]	279	200	2.06	7	17	0.14	123	1.40	0.42	3	0.038	

Footnotes: 1) Sample status

Cases

SEMITRANS 3





Dimensions in mm